MY2305

-20V P-Channel Enhancement ModeMOSFET

General Description

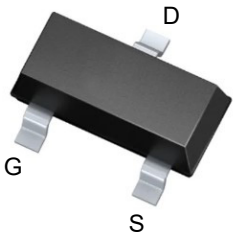
The MY2305 is the high cell density trenched P-CH MOSFET,which provide excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load s witch applications.

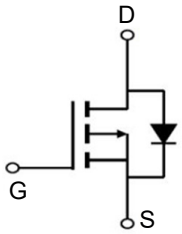
Features

V_{DSS}	-20	V
I_D	-4.2	A
$R_{DS(ON)}$(atV_{GS}=-4.5V)	35	mΩ
$R_{DS(ON)}$(atV_{GS}=-2.5V)	39	mΩ

Application

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY2305	SOT-23	2305	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-4.2	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-3.0	A
I_{DM}	Pulsed Drain Current[2]	-16	A
P_D@T_A=25℃	Total Power Dissipation[3]	1.31	W
P_D@T_A=70℃	Total Power Dissipation[3]	0.84	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -20V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-0.4	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}= -4.5V, I_D= -4.1A	-	35	42	mΩ
		V_{GS}= -2.5V, I_D= -3A	-	39	53	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -10V, V_{GS}=0V, f=1.0MHz	-	830	-	pF
C_{oss}	Output Capacitance		-	132	-	pF
C_{rss}	Reverse Transfer Capacitance		-	85	-	pF
Q_g	Total Gate Charge	V_{DS}= -10V, I_D= -2A, V_{GS}= -4.5V	-	8.8	-	nC
Q_{gs}	Gate-Source Charge		-	1.4	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.9	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -10V, I_D= -3.3A, R_G= 1Ω, V_{GEN}= -4.5V	-	10	-	ns
t_r	Turn-on Rise Time		-	32	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	50	-	ns
t_f	Turn-off Fall Time		-	51	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5.0	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -4.1A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Switching Time Test Circuit and Waveforms

Figure1: Output Characteristics

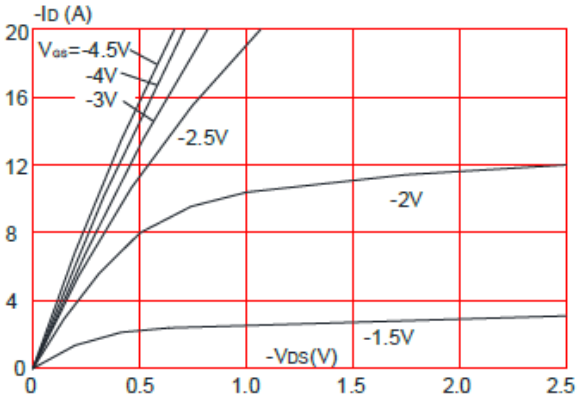


Figure 2: Typical Transfer Characteristics

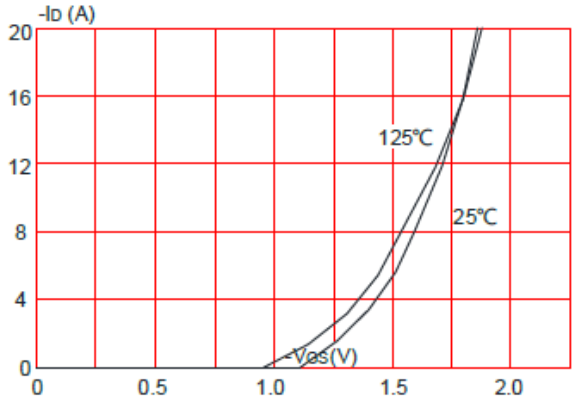


Figure 3: On-resistance vs. Drain Current

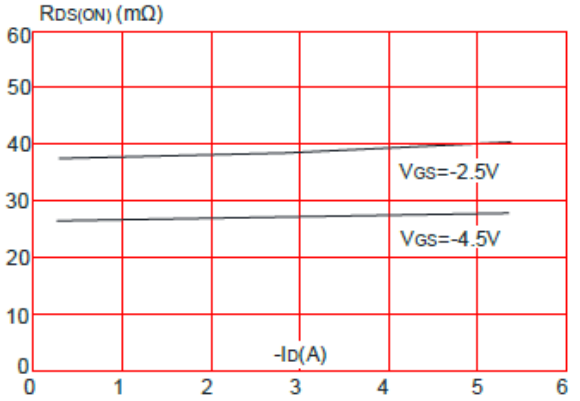


Figure 4: Body Diode Characteristics

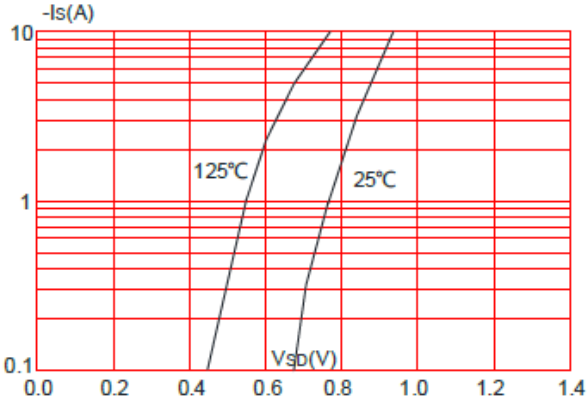


Figure 5: Gate Charge Characteristics

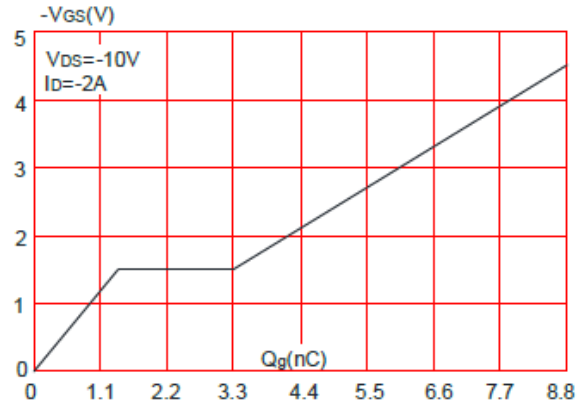


Figure 6: Capacitance Characteristics

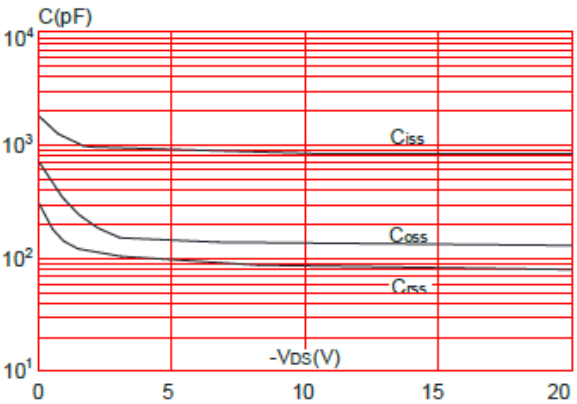


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

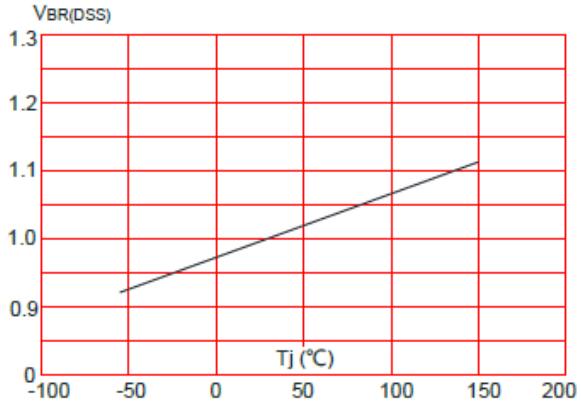


Figure 8: Normalized on Resistance vs. Junction Temperature

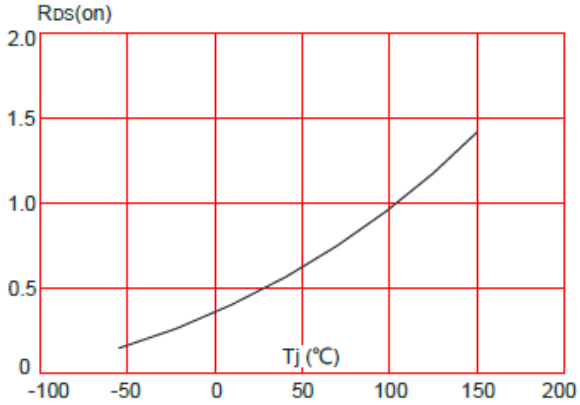


Figure 9: Maximum Safe Operating Area

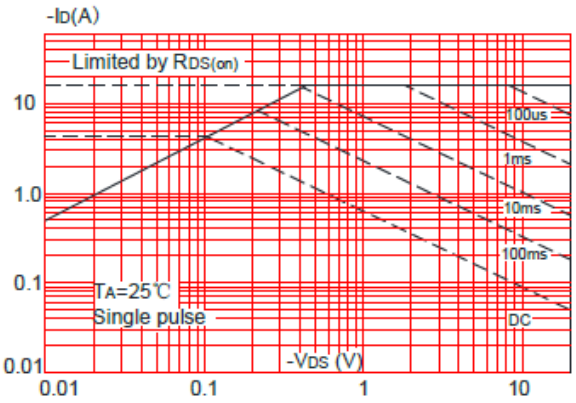


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

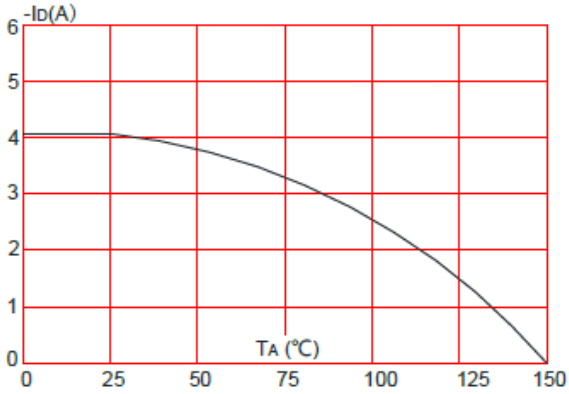
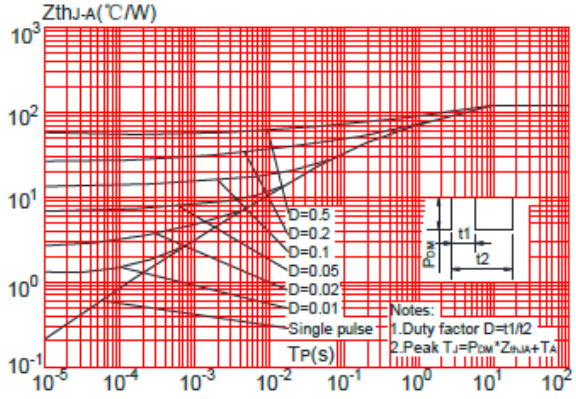
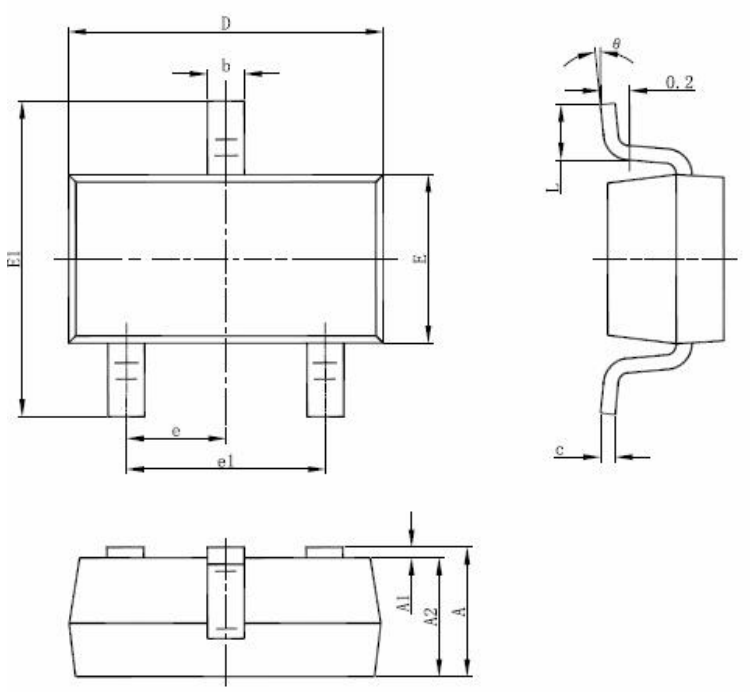


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°